STP80PF55-VB Datasheet

P-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[c]
- 60	0.0074 at V_{GS} = - 10 V	- 90
	0.0094 at V_{GS} = - 4.5 V	- 90

FEATURES

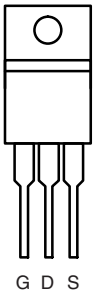
- Trench Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

RoHS COMPLIANT

APPLICATIONS

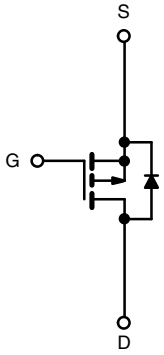
- DC/DC Primary Switch

TO-220AB



Top View

Drain connected to Tab



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	- 60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current (T_J = 175 °C)[c]	T_C = 25 °C	I_D	- 90	A
	T_C = 125 °C		- 67	
Pulsed Drain Current		I_{DM}	- 200	
Avalanche Current	L = 0.1 mH	I_{AS}	- 65	
Single Pulse Avalanche Energy[a]		E_{AS}	211	mJ
Power Dissipation	T_C = 25 °C	P_D	250[b]	W
	T_A = 25 °C		2.4	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	**Symbol**	**Limit**	**Unit**
Junction-to-Ambient Free Air	R_{thJA}	62	°C/W
Junction-to-Case	R_{thJC}	0.6	

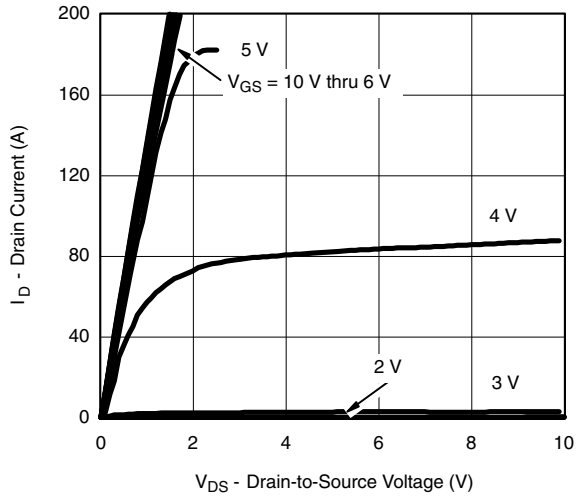
Notes:
a. Duty cycle ≤ 1 %.
b. See SOA curve for voltage derating.
c. Limited by package.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 60			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 1		- 3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 60 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 60 V, V_{GS} = 0 V, T_J = 125 °C			- 50	
		V_{DS} = - 60 V, V_{GS} = 0 V, T_J = 175 °C			- 250	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = - 5 V, V_{GS} = - 10 V	- 120			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 30 A		0.0074		Ω
		V_{GS} = - 10 V, I_D = - 30 A, T_J = 125 °C		0.0150		
		V_{GS} = - 10 V, I_D = - 30 A, T_J = 175 °C		0.0190		
		V_{GS} = - 4.5 V, I_D = - 20 A		0.0094		
Forward Transconductance[a]	g_{fs}	V_{DS} = - 15 V, I_D = - 30 A	20			S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = - 25 V, f = 1 MHz		9200		pF
Output Capacitance	C_{oss}			975		
Reverse Transfer Capacitance	C_{rss}			760		
Total Gate Charge[c]	Q_g	V_{DS} = - 30 V, V_{GS} = - 10 V, I_D = - 90 A		160	240	nC
Gate-Source Charge[c]	Q_{gs}			40		
Gate-Drain Charge[c]	Q_{gd}			36		
Gate Resistance	R_g	f = 1.0 MHz		3		Ω
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = - 30 V, R_L = 0.33 Ω $I_D \cong$ - 90 A, V_{GEN} = - 10 V, R_g = 2.5 Ω		20	30	ns
Rise Time[c]	t_r			190	285	
Turn-Off Delay Time[c]	$t_{d(off)}$			140	210	
Fall Time[c]	t_f			300	450	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)[b]						
Continuous Current	I_S				- 90	A
Pulsed Current	I_{SM}				- 200	
Forward Voltage[a]	V_{SD}	I_F = - 50 A, V_{GS} = 0 V		- 1.0	- 1.5	V
Reverse Recovery Time	t_{rr}	I_F = - 50 A, dI/dt = 100 A/µs		60	90	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			- 3	- 4.5	A
Reverse Recovery Charge	Q_{rr}			0.09	0.2	µC

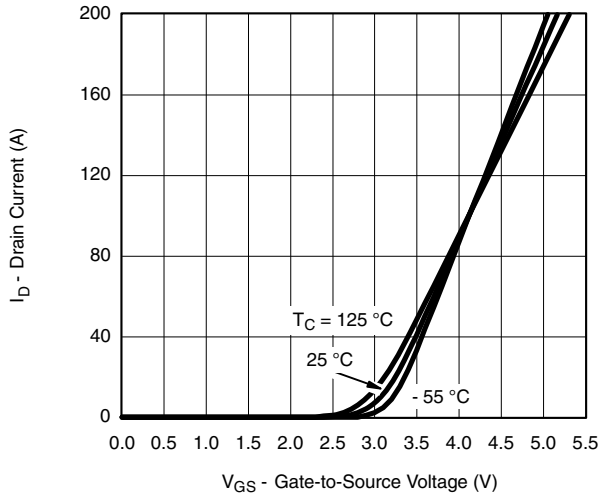
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

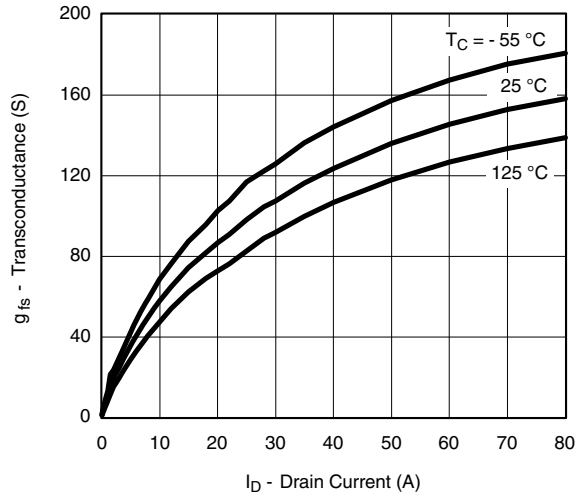
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



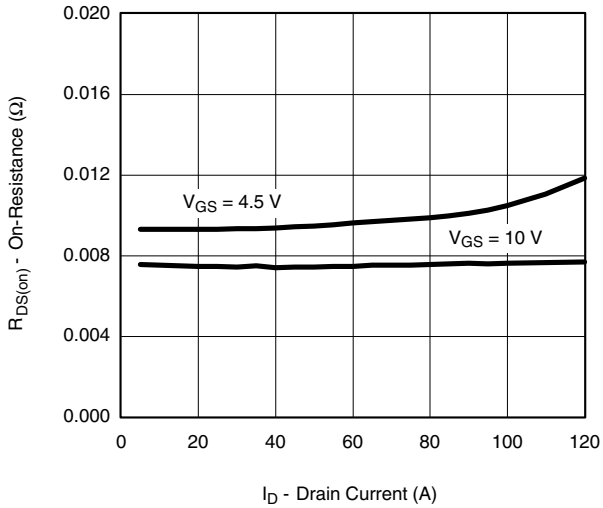
Output Characteristics



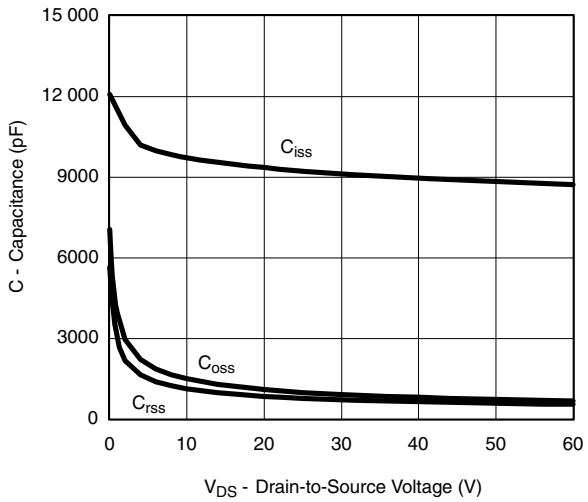
Transfer Characteristics



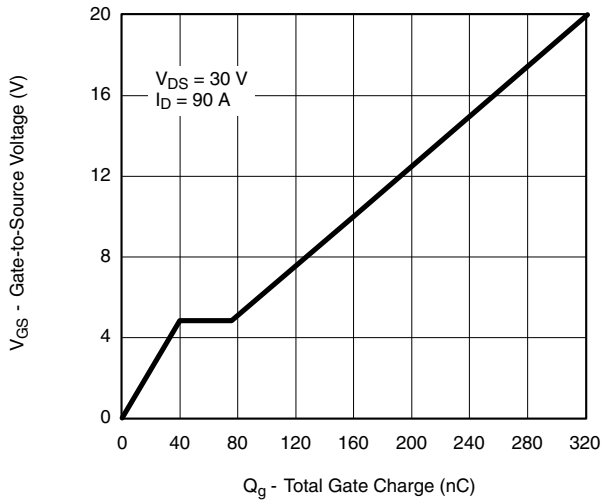
Transconductance



On-Resistance vs. Drain Current

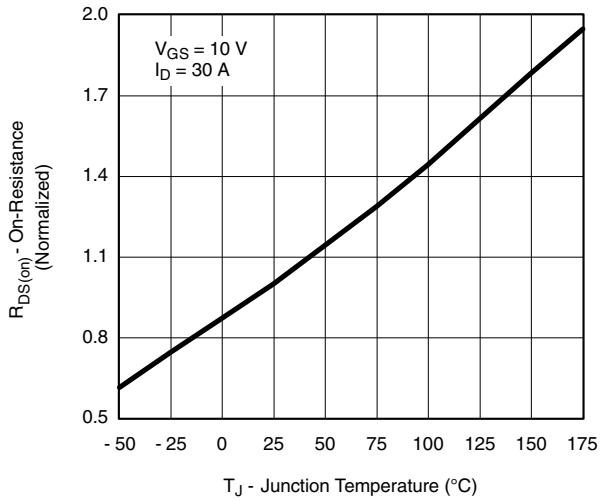


Capacitance

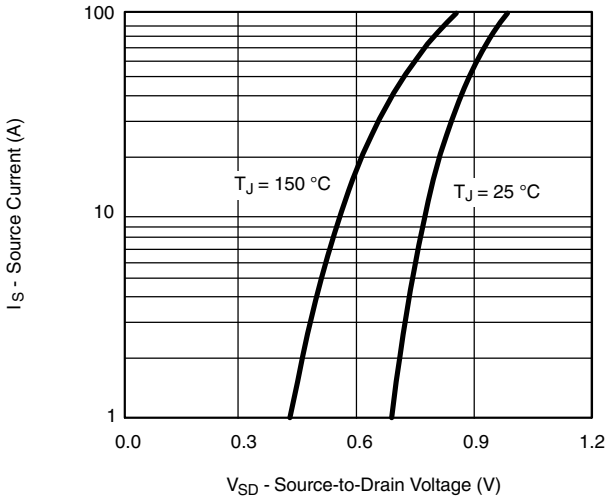


Gate Charge

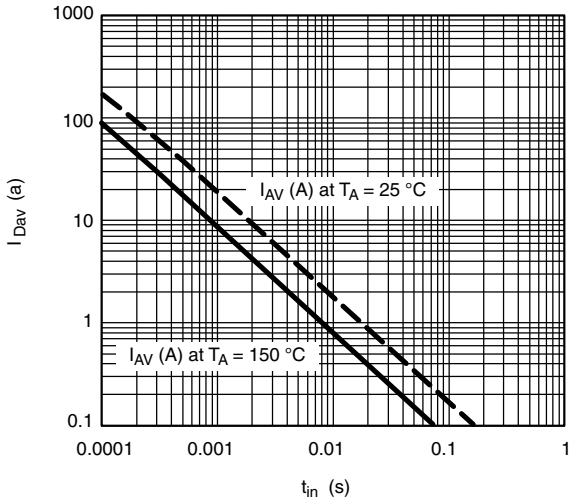
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



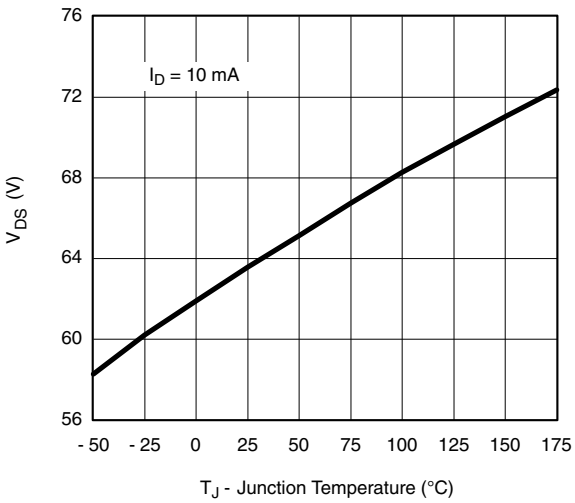
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

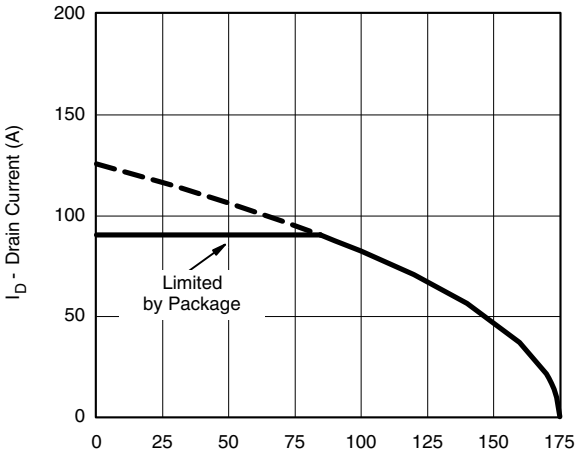


Avalanche Current vs. Time

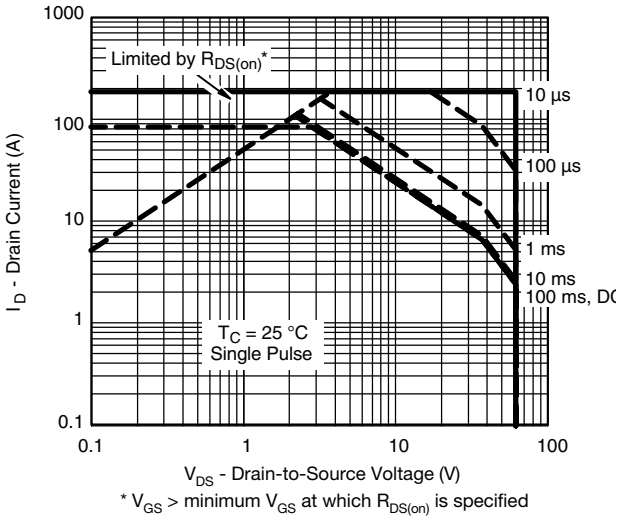


Drain Source Breakdown vs. Junction Temperature

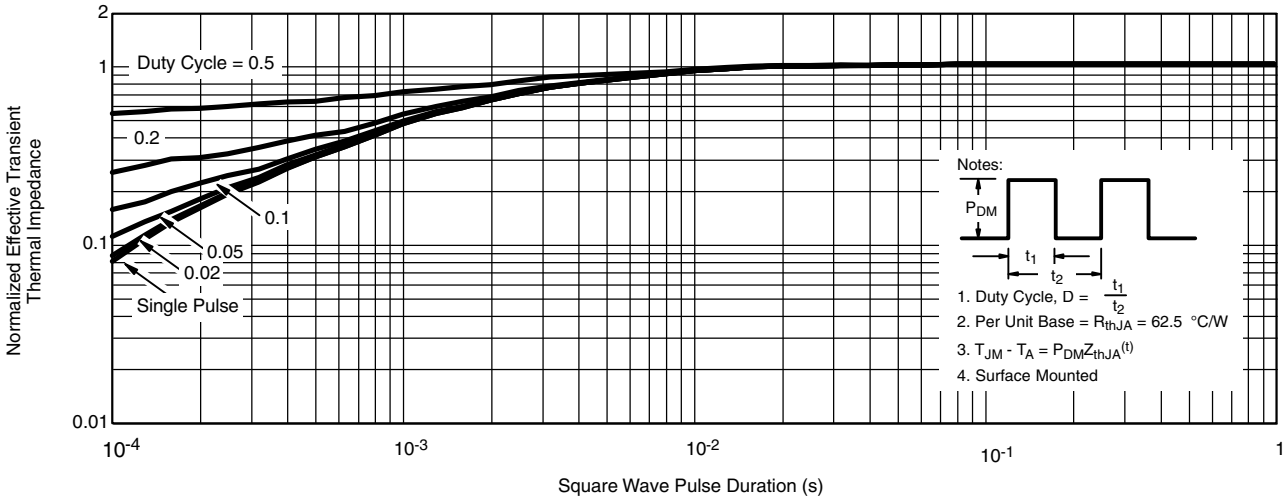
THERMAL RATINGS



Maximum Avalanche and Drain Current vs. Case Temperature

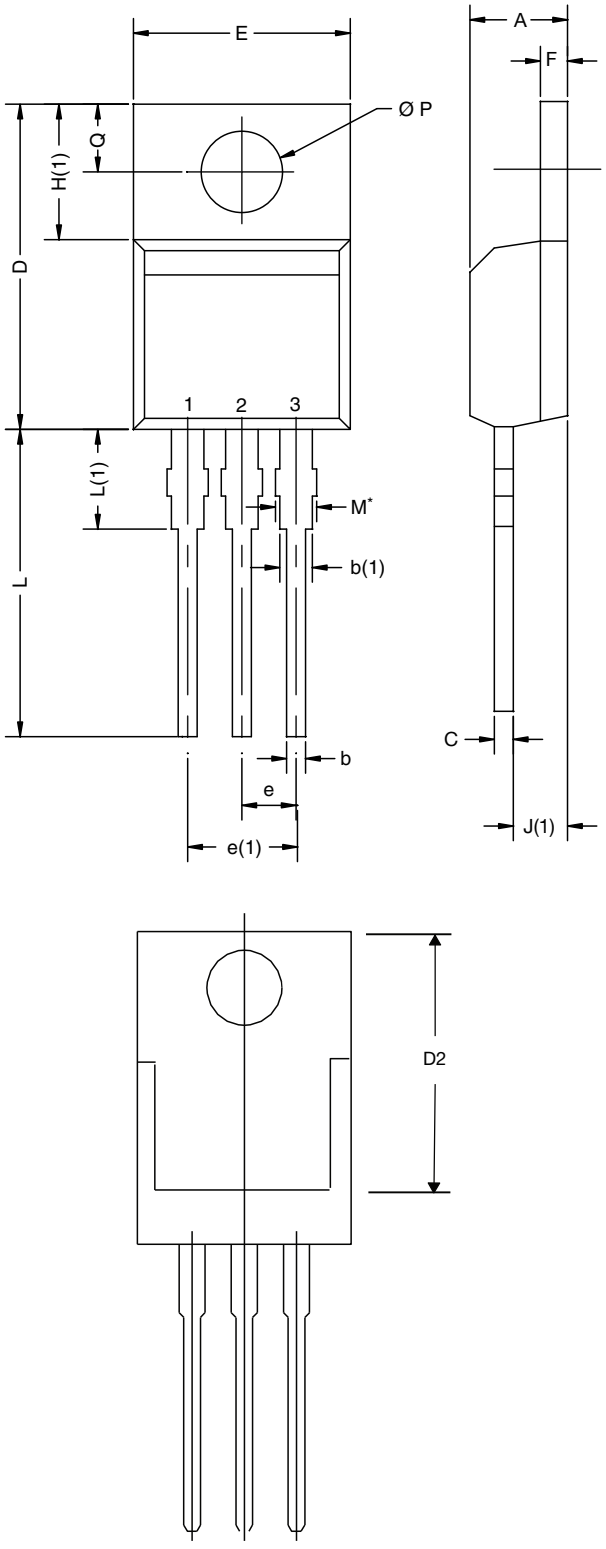


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471				

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM

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